

ABSTRACT

A semiconductor device includes an active pattern on a substrate with first and second regions; first and second source/drain regions on the first and second regions; first and second source/drain contacts on the first and second source/drain regions; and a separation structure intersecting the active pattern between the first and second source/drain contacts, and extending into the active pattern between the first and second source/drain regions, wherein an upper surface of the second source/drain contact is higher than an upper surface of the first source/drain contact, and wherein the separation structure has an asymmetrical structure having an upper surface of a first portion adjacent to the first source/drain contact higher than an upper surface of a second portion adjacent to the second source/drain contact.

FIG. 5